

COMPAD

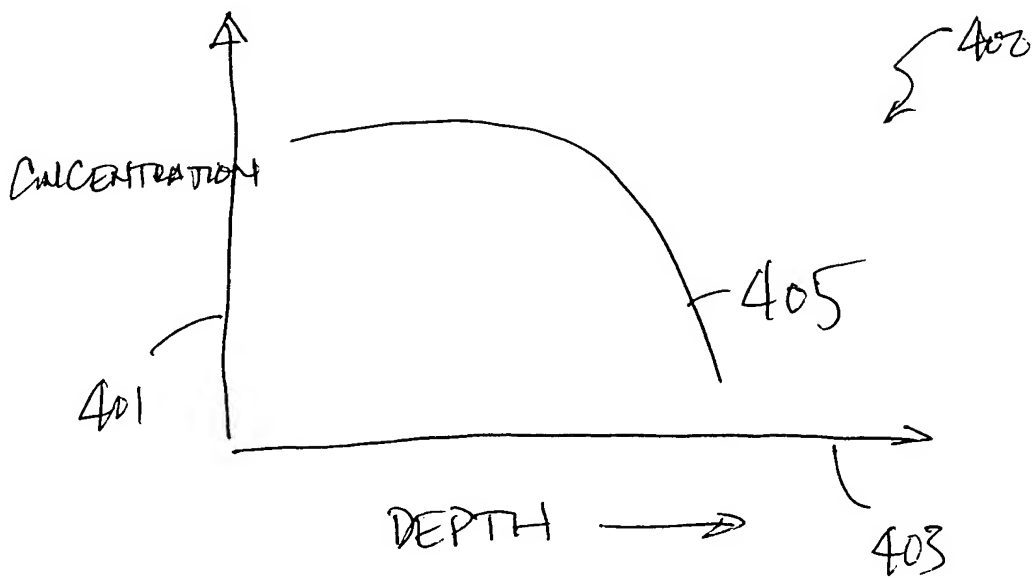


FIG. 4

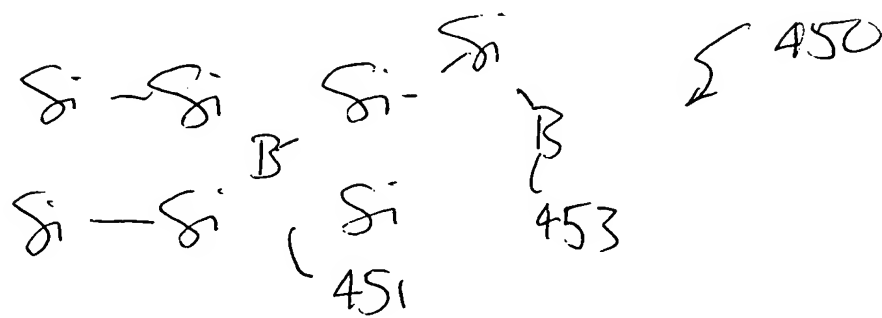


FIG. 4A

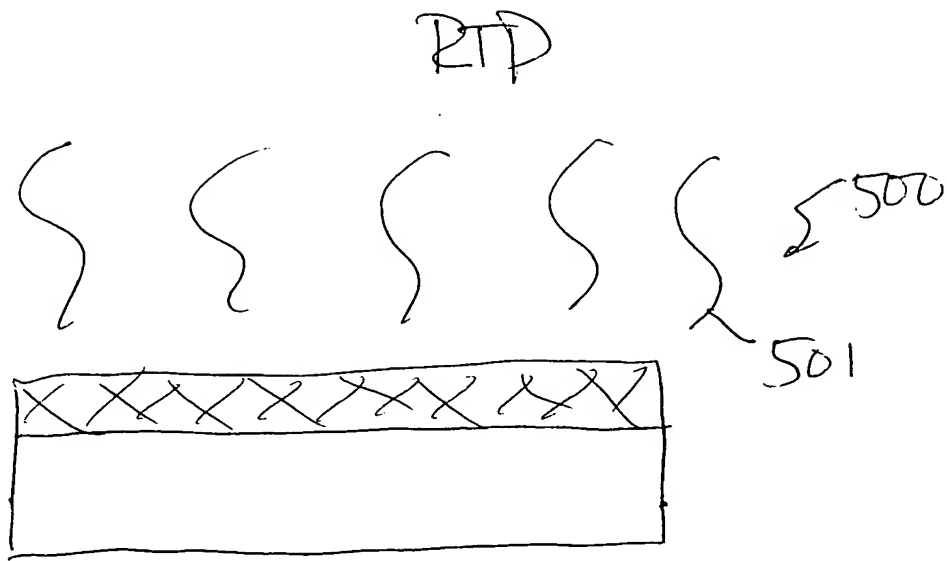


FIG. 5

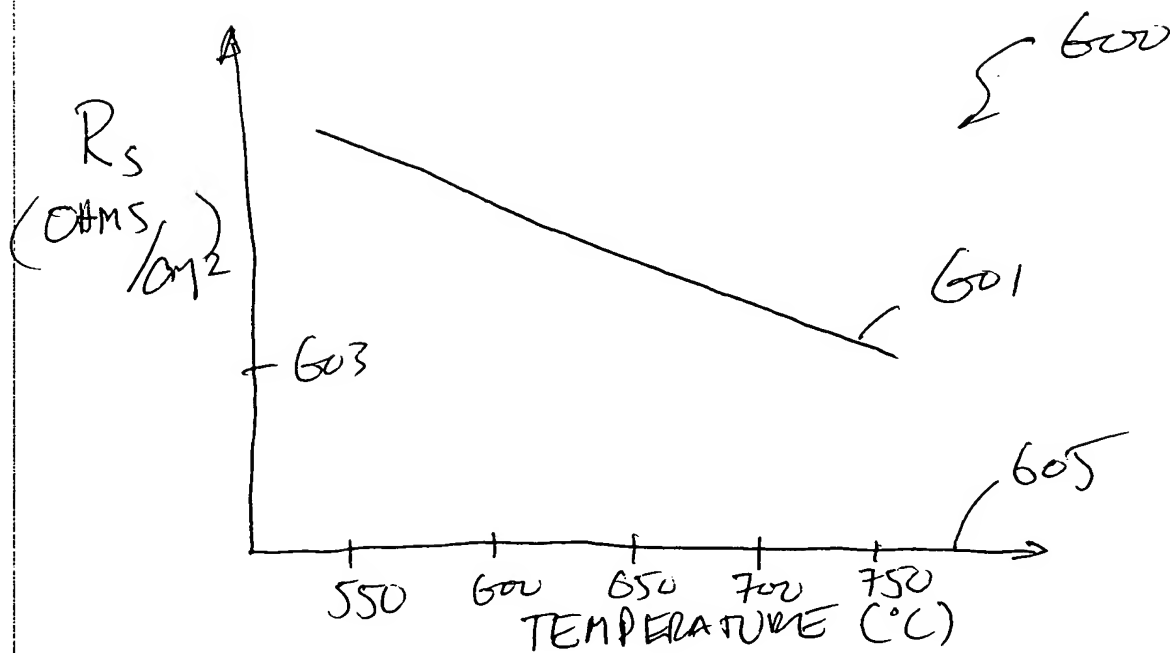
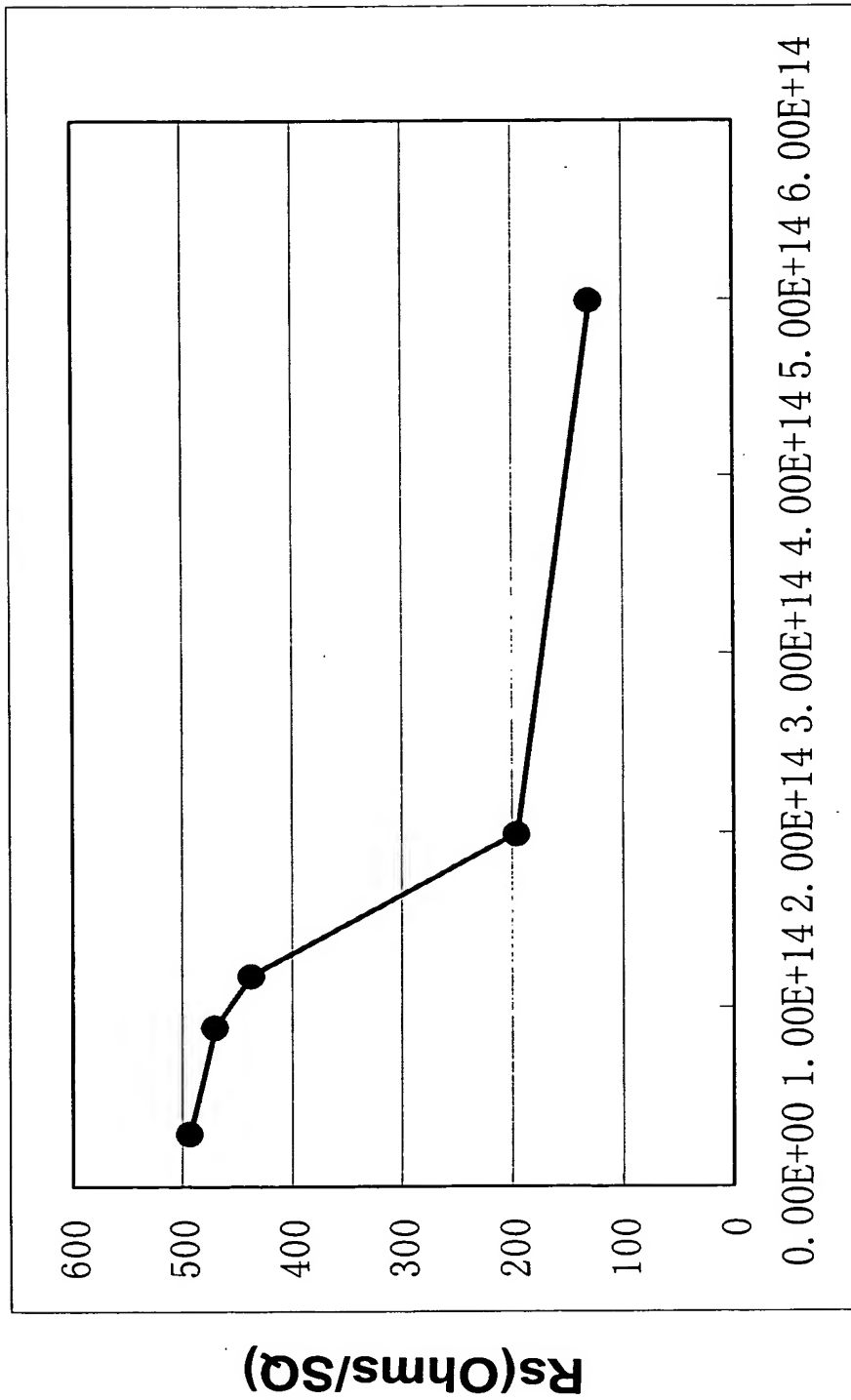


FIG. 6

Low temperature monitor



Dosage(atom/cm²)

Figure 7: Changes of R_s as a function of implant dosage of silicon, Boron dosage unchanged($3.5E^{15}$).

FIG. 7

Low temperature monitor

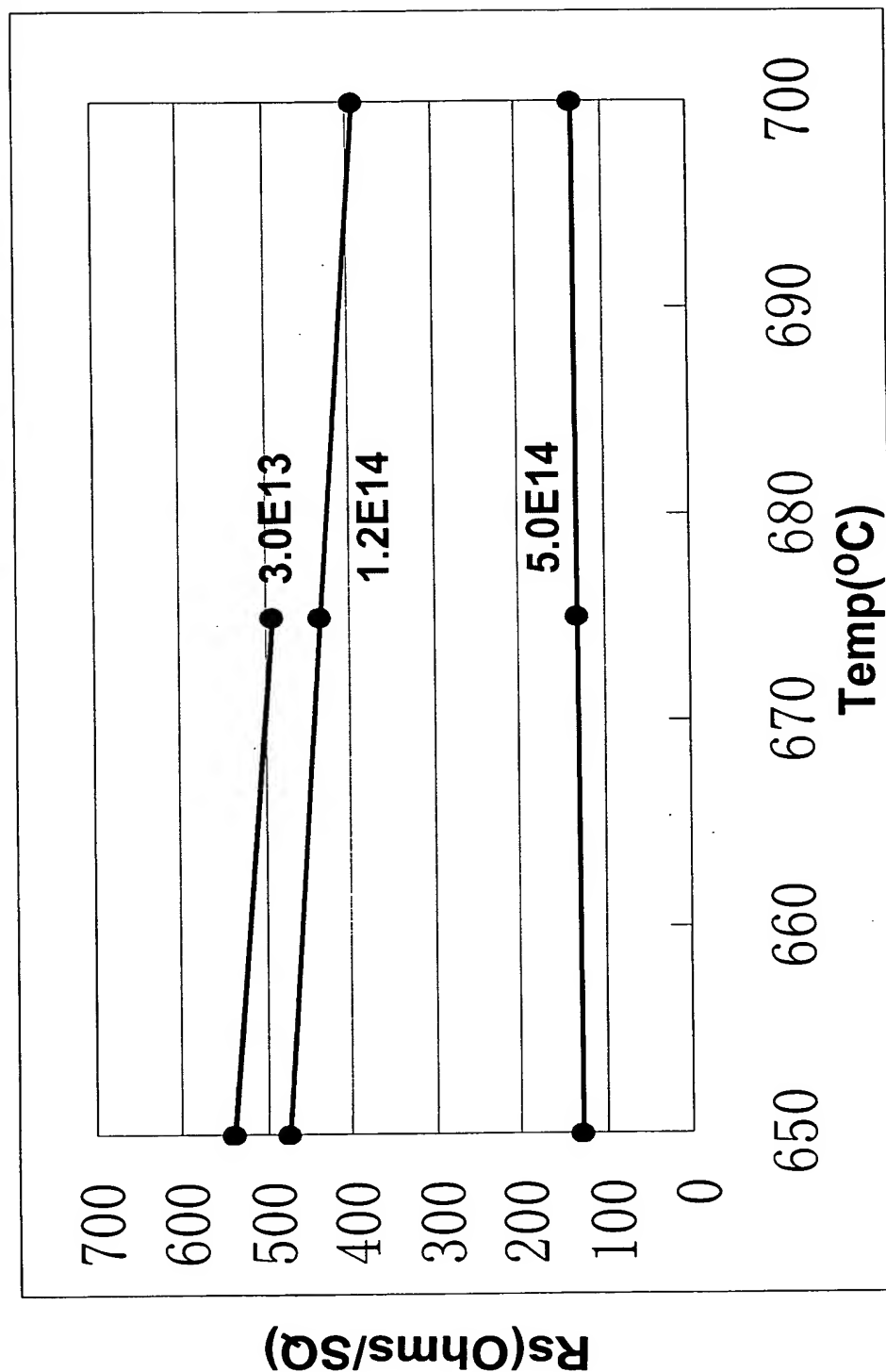


Figure 8: The dependence of R_s on annealing temperature. The implant dose of silicon varied from $3.0E13$ to $5.0E14$, Boron dosage unchanged ($3.5E15$).

FIG. 8